

General Description

The CMSA045N10 uses advanced SGT technology to provide excellent RDS(ON). This is suitable device for Synchronous Rectification For Server and general purpose applications.

Features

- Low On-Resistance
- 100% avalanche tested
- Small Footprint (5x6 mm) for Compact Design
- RoHS Compliant

Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	100	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_C=25^\circ\text{C}$	Continuous Drain Current	100	A
$I_D@T_C=100^\circ\text{C}$	Continuous Drain Current	70	A
I_{DM}	Pulsed Drain Current	400	A
EAS	Single Pulse Avalanche Energy ¹	272	mJ
$P_D@T_C=25^\circ\text{C}$	Total Power Dissipation	150	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient(min. footprint)	---	54	$^\circ\text{C}/\text{W}$
$R_{\theta JC}$	Thermal Resistance Junction-case	---	0.83	$^\circ\text{C}/\text{W}$

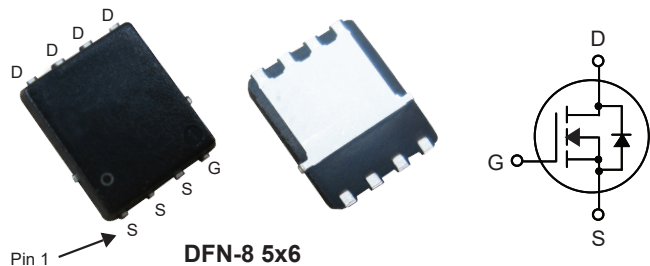
Product Summary

BVDSS	$R_{DS(on)}$ max.	ID
100V	4.5mΩ	100A

Applications

- Battery management
- High Frequency Switching and Synchronous Rectification

DFN-8 5x6 Pin Configuration



Type	Package	Marking
CMSA045N10	DFN-8 5x6	CMSA045N10

Electrical Characteristics($T_J=25^{\circ}\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V$, $I_D=250\mu A$	100	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=10V$, $I_D=28A$	---	3.9	4.5	mΩ
		$V_{GS}=4.5V$, $I_D=25A$	---	5	6	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}$, $I_D=250\mu A$	1.0	---	3.0	V
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=100V$, $V_{GS}=0V$	---	---	1	μA
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V$, $V_{DS}=0V$	---	---	±100	nA
g_{fs}	Forward Transconductance	$V_{DS}=10V$, $I_D=20A$	---	40	---	S
R_g	Gate Resistance	$V_{DS}=0V$, $V_{GS}=0V$, $f=1\text{MHz}$	---	2.0	---	Ω
Q_g	Total Gate Charge	$I_D=40A$ $V_{DS}=50V$ $V_{GS}=10V$ (Note 2)	---	60	---	nC
Q_{gs}	Gate-Source Charge		---	16	---	
Q_{gd}	Gate-Drain Charge		---	11	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=50V$ $V_{GS}=10V$ $R_{G_{ext}}=3\Omega$ (Note 2)	---	14	---	ns
T_r	Rise Time		---	42	---	
$T_{d(off)}$	Turn-Off Delay Time		---	46	---	
T_f	Fall Time		---	19	---	
C_{iss}	Input Capacitance	$V_{DS}=25V$, $V_{GS}=0V$, $f=1\text{MHz}$	---	3600	---	pF
C_{oss}	Output Capacitance		---	1600	---	
C_{rss}	Reverse Transfer Capacitance		---	100	---	

Diode Characteristics

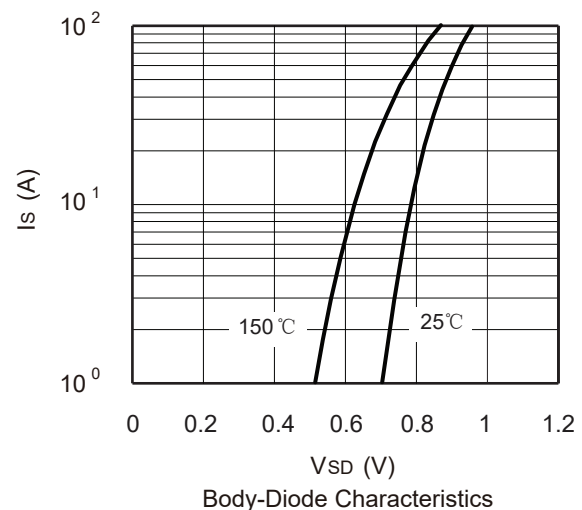
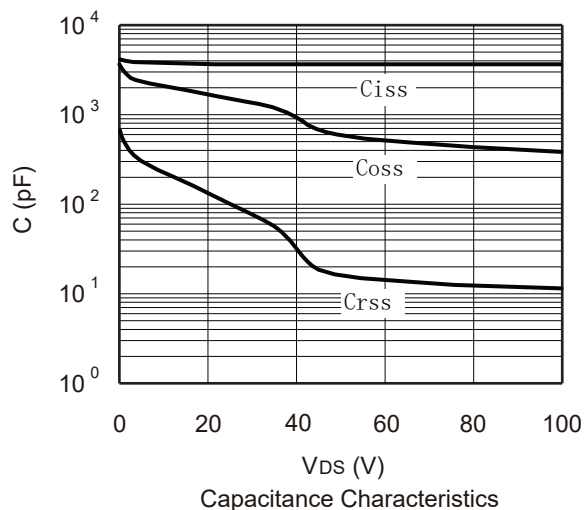
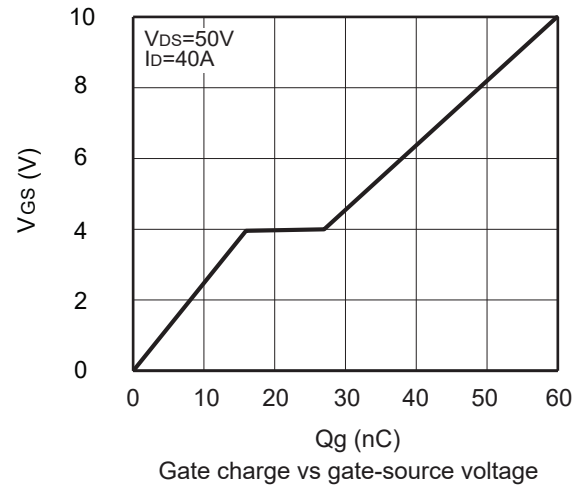
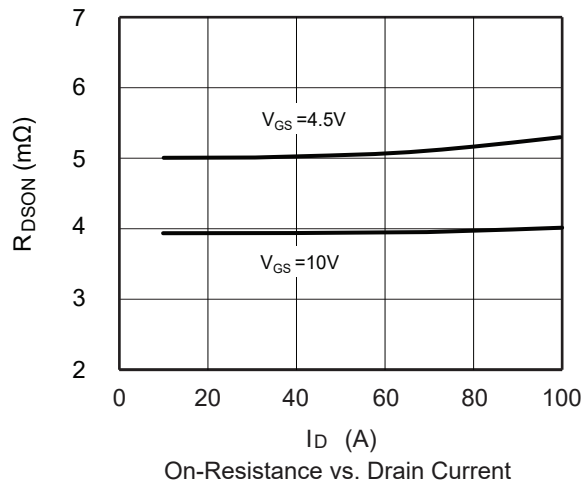
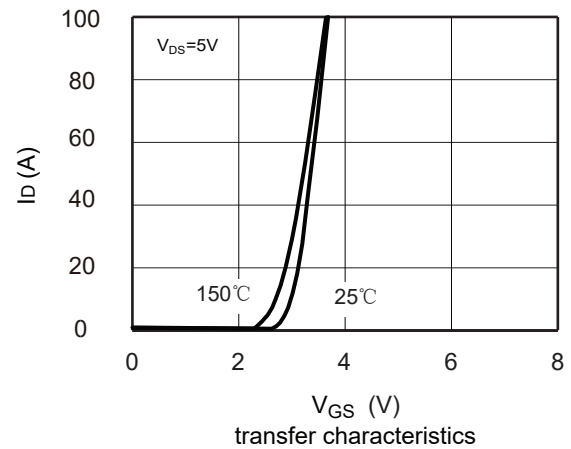
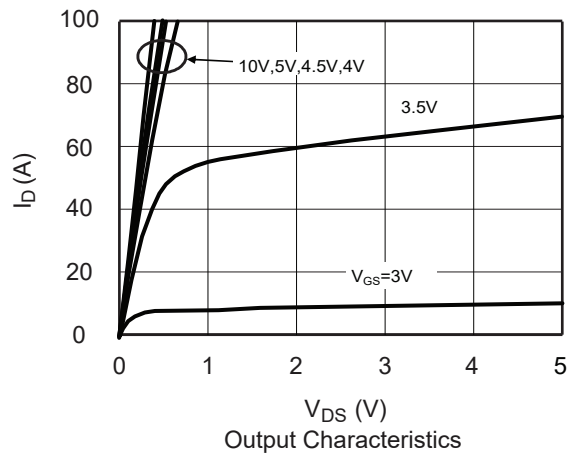
Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current	$V_G=V_D=0V$, Force Current	---	---	100	A
I_{SM}	Pulsed Source Current		---	---	400	A
V_{SD}	Diode Forward Voltage	$V_{GS}=0V$, $I_S=25A$, $T_J=25^{\circ}\text{C}$	---	0.82	1.2	V

Note :

- 1.The EAS data shows Max. rating . The test condition is $V_{DD}=50V$, $V_{GS}=10V$, $L=0.5\text{mH}$, $I_{AS}=33A$.
- 2.Guaranteed by design, not subject to production testing.

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Cmos assumes no liability for customers' product design or applications.
Cmos reserves the right to improve product design ,functions and reliability without notice.

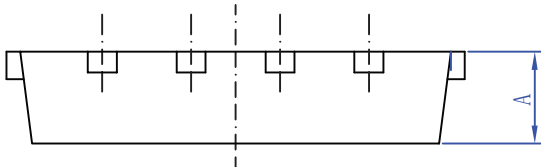
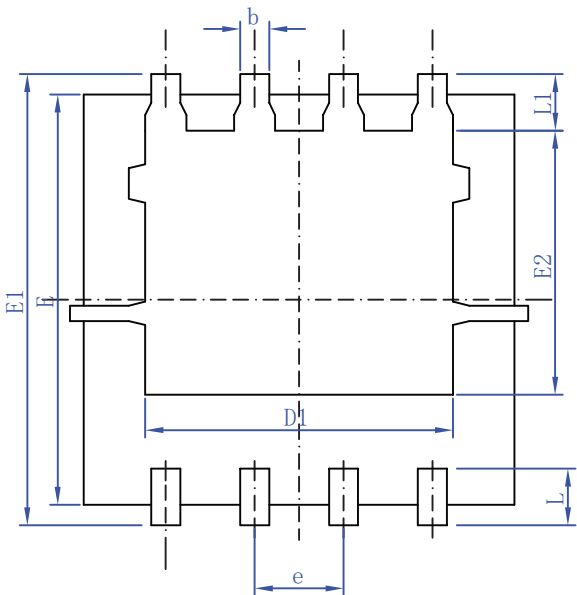
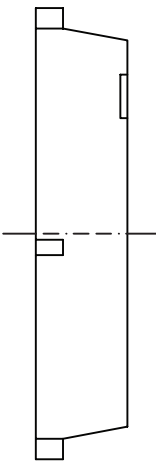
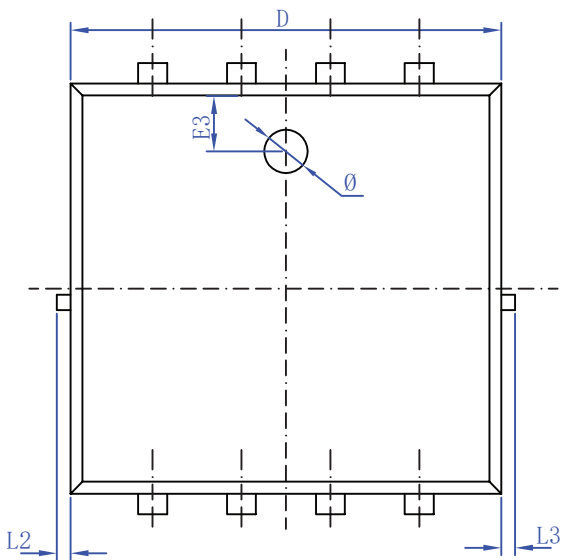
Typical Characteristics



Package Dimension

DFN-8 5x6

Unit :mm



注：
1. 未注公差±0.05未标注圆角R max=0.25

Dimensions In Millimeters			
Symbol	Min.	Max.	Ave.
A	0.900	1.100	1.000
D	4.950	5.150	5.050
D1	3.850	4.250	4.050
E	5.750	5.950	5.850
E1	5.950	6.350	6.150
E2	3.300	3.700	3.500
E3	0.900	1.300	1.100
b	0.250	0.350	0.300
e	1.220	1.320	1.270
L	0.585	0.785	0.685
L1	0.525	0.725	0.625
Ø	1.000	1.400	1.200
L2	0~0.100		
L3	0~0.100		